

Thermoelectric generators as self-oscillating heat engines

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In the previous paper [1] a model of a solar cell has been proposed in which the non-periodic source of energy - photon flux - drives the collective periodic motion of electrons in a form of plasma oscillations. Subsequently, plasma oscillations are rectified by the p-n junction diode into the direct current (work). This approach makes a solar cell similar to standard macroscopic heat motors or turbines which always contain two heat baths, the working medium and the periodically moving piston or rotor. Here, a very similar model is proposed in order to describe the operation principles of thermoelectric generators based either on bimetallic or semiconductor p-n junctions. Again plasma oscillation corresponds to a piston and sunlight is replaced by a hot bath. The mathematical formalism is based on the Markovian master equations which can be derived in a rigorous way from the underlying Hamiltonian models and are consistent with the laws of thermodynamics.

INTRODUCTION

While the macroscopic heat motors or turbines contain always periodically moving elements like pistons, flywheels or rotors [2],[3], the photovoltaic devices, thermoelectric generators or biological engines driven either by sunlight (photosynthesis) or chemical energy seem, according to the standard wisdom, to avoid any self-oscillation mechanisms. On the other hand extensive theoretical studies of quantum heat engines within the formalism of quantum open systems [4] - [8] show that the process of work extraction must involve a work reservoir being a system of a single degree of freedom and executing an oscillatory motion which in the semi-classical limit can be replaced by the periodic external driving. The presence of such a system is even necessary to properly define the notion of work as a deterministic form of energy. It suggests that for the examples mentioned above a certain “hidden” self-oscillation mechanism of work generation must also be present. Indeed, as already noticed the standard picture of current generation as caused by the emerging electric field in a junction cannot be correct because a DC current cannot be driven in a closed circuit by a purely electrical potential difference [9]. In the previous paper [1] it was shown that the consistent description of work generation by a solar cell can be formulated introducing a work reservoir in a form of THz plasma oscillations.

The aim of the present contribution is to show that a very similar model can explain the operation principles of thermoelectric generators. The basic difference between semiconductor and bimetallic devices concerns the frequency of plasma oscillations. For doped semiconductors plasma frequencies are in the THz domain (low infrared) [10], [11] and can be treated as slow while for metals they correspond to the ultraviolet region (PHz = 10^{15} Hz) and therefore are too fast to be effectively coupled to the thermal motion of a lattice. However, it is argued in the Appendix, using hydrodynamical model of electron gas, that under reasonable assumptions there should exist THz modes of plasma oscillations in bimetal-

lic contacts.

HEAT ENGINE WITH A SLOW PISTON

Consider a simplified version of the generic quantum heat engine model introduced in [4] and successfully used in [1] in the context of solar cells. The system, corresponding to the “working medium” interacts weakly with two heat baths at different temperatures. The macroscopic piston is described by the external driving $V(t)$ added to the free Hamiltonian H_0 of the system.

For slowly varying $V(t)$ (in comparison to the fast internal dynamics) the irreversible evolution of the system’s time-dependent reduced density matrix $\rho(t)$ satisfies the following Markovian master equation (MME)

$$\frac{d}{dt}\rho(t) = -i[H(t), \rho(t)] + \mathcal{L}(t)\rho(t), \quad (1)$$

where $H(t) = H_0 + V(t)$ is the total Hamiltonian of the system and $\mathcal{L}(t)$ describes the action of the baths on the system ($\hbar = k_B = 1$).

The periodic driving executed by a large semi-classical oscillator commutes with the system Hamiltonian and reads

$$V(t) = g(\sin \Omega t) M, \quad [H_0, M] = 0, \quad (2)$$

where $g \ll 1$ is a small amplitude of oscillations. The dissipative generator $\mathcal{L}(t)$ obtained by the weak coupling limit procedure is a function of the magnitude of perturbation and can be written as

$$\mathcal{L}(t) \equiv \mathcal{L}[\xi(t)], \quad \xi(t) = g \sin \Omega t. \quad (3)$$

For all ξ the generators $\mathcal{L}[\xi]$ commute and possess the stationary states $\bar{\rho}[\xi]$ satisfying the identities

$$\mathcal{L}[\xi]\bar{\rho}[\xi] = 0, \quad \mathcal{L}'[\xi]\bar{\rho}[\xi] = -\mathcal{L}[\xi]\bar{\rho}'[\xi] \quad (4)$$

where $\mathcal{L}'[\xi] \equiv \frac{d}{d\xi}\mathcal{L}[\xi]$, $\bar{\rho}'[\xi] \equiv \frac{d}{d\xi}\bar{\rho}[\xi]$.

Formula for power

The power $P(t)$ provided by the engine and the net heat current $J(t)$ supplied by the baths are defined as [4]

$$P(t) = -\text{Tr}\left(\rho(t)\frac{dH(t)}{dt}\right), \quad J(t) = \text{Tr}\left(H(t)\frac{d\rho(t)}{dt}\right). \quad (5)$$

Those definitions are the only ones which are consistent with the first and second law of thermodynamics and the time-dependence of the Hamiltonian is necessary to define work. The stationary average power output of the engine reads

$$\bar{P} = -g\Omega \lim_{t_0 \rightarrow \infty} \frac{1}{t_0} \int_0^{t_0} \text{Tr}\left(\rho(t)M\right) \cos \Omega t dt. \quad (6)$$

Expanding the average power with respect to g one obtains the second order approximation [1]

$$\bar{P} = -\frac{1}{2}g^2 \text{Tr}\left(\bar{\rho}'[0] \frac{\Omega^2}{\Omega^2 + \mathcal{L}^{*2}[0]} \mathcal{L}^*[0]M\right), \quad (7)$$

where $\mathcal{L}^*[0]$ is the Heisenberg picture counterpart of the Schroedinger picture generator $\mathcal{L}[0]$. To derive the final expression one assumes that, although the modulation is slow with respect to the intrinsic motion of the system, its frequency is much higher than the relaxation rate of the observable M hidden in $\mathcal{L}^*[0]$. Then, we have

$$\bar{P} = -\frac{1}{2}g^2 \text{Tr}\left(\bar{\rho}'[0] \mathcal{L}^*[0]M\right). \quad (8)$$

The lowest order formula (8) is still consistent with thermodynamics [1] and is the basic one for the further analysis of thermoelectric generators. Notice, that the stationary output power is proportional to the square of the amplitude of piston oscillations. This amplitude is a free parameter which is determined by the energy flux from the hot bath and the load attached to the oscillator (e.g. the resistance of the external electric circuit).

MODEL OF THERMOELECTRIC GENERATOR

The model of thermoelectric generator is illustrated on Fig.1. The working medium is an electron gas distributed in two boxes A and B , corresponding to different materials, metals or doped semiconductors, connected by a junction. The electrostatic potential jump through the junction denoted by E_g is typically of the order of few eV . We assume that in the case of metals the density of electrons in the box A is lower than in B what implies that potential energy of the electron in the box A is higher than in the box B . For semiconductors the box A is a p-type and the box B a n-type doped material. The hot bath interacts with the electrons in the interface region influencing their transport through the junction

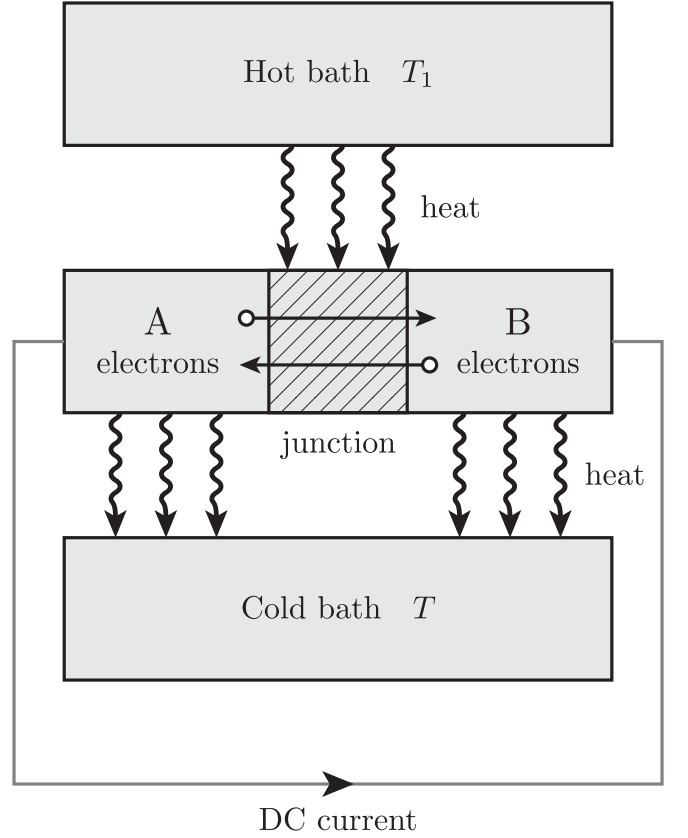


FIG. 1. **Model of thermoelectric generator.** Bimetallic or p-n junction is heated by a hot bath increasing the transition rate between both regions. The electrons in bulk are cooled down by a cold bath. Rectified plasma oscillations produce a net flow of electrons from the region with their higher density (box B) to the lower one (box A).

while the cold bath at the ambient temperature cools down the electrons in the bulk. In the junction region an interface between two different material is formed with the local concentration of charges and build-in electrostatic potential. One assumes the existence of collective charge oscillations localized at the junction with typical frequencies in THz domain. For semiconductor devices such oscillations are experimentally confirmed and interpreted as plasma oscillations with the plasma frequency

$$\omega_p = \sqrt{\frac{ne^2}{m_*\epsilon_0}}, \quad (9)$$

where n is a density of charge carriers and m_* their effective mass. The bimetallic junction is more complicated as the bulk and surface plasma oscillations in metals possess frequencies in the PHz domain ($10^{15} Hz$) and hence cannot be effectively excited by thermal phonons. In the Appendix the mechanism of slow coherent charge oscillations is proposed which is related to the particular physical structure of metal-metal junctions.

The electrons in two boxes A and B are described by

two sets of the annihilation and creation operators $a_{\mathbf{k}}$, $a_{\mathbf{k}}^\dagger$ and $b_{\mathbf{l}}$, $b_{\mathbf{l}}^\dagger$, respectively, subject to canonical anticommutation relations. The electrons are treated as non-interacting fermions moving in a self-consistent potential with the unperturbed Hamiltonian

$$H_0 = \sum_{\mathbf{k}} E_a(\mathbf{k}) a_{\mathbf{k}}^\dagger a_{\mathbf{k}} + \sum_{\mathbf{l}} E_b(\mathbf{l}) b_{\mathbf{l}}^\dagger b_{\mathbf{l}}. \quad (10)$$

In a junction a non-homogeneous free carrier distribution created in a self-consistent build-in potential can be perturbed producing collective plasma oscillations with the frequency Ω . Those oscillations modulate periodically the Hamiltonian (10) but the detailed mechanism is slightly different for the semiconductor and bimetallic junctions (see Appendix for the derivations). In both cases the associated time-dependent perturbation which should be added to the electronic Hamiltonian (10), is proportional to the difference of electron densities in the boxes B and A and has a mean-field form ($\xi(t) = g \sin \Omega t$)

$$\xi M = \xi E_g V_J \left(\frac{1}{V_B} \sum_{\mathbf{l}} b_{\mathbf{l}}^\dagger b_{\mathbf{l}} - \frac{1}{V_A} \sum_{\mathbf{k}} a_{\mathbf{k}}^\dagger a_{\mathbf{k}} \right). \quad (11)$$

Here, ξ is a small dimensionless parameter describing the magnitude of deformation, V_A, V_B volumes of the boxes, V_J is the effective volume of the junction region and E_g is the relevant energy scale chosen here to be the potential jump across the junction. Remember, that for the semiconductor p-n junction the box A corresponds to the “p” part and B to the “n” part. In this case $-a_{\mathbf{k}}^\dagger a_{\mathbf{k}}$ should be rather interpreted as the number operator of holes minus an irrelevant constant.

The interaction with two independent heat bath is described by the sum of two terms: $\mathcal{L}_c$ for the cold bath at the ambient temperature T and $\mathcal{L}_h$ for the hot bath at the temperature $T_1 > T$. The coupling to the cold bath thermalizes electrons in both boxes independently and hence preserves separately both electron numbers $\sum_{\mathbf{k}} a_{\mathbf{k}}^\dagger a_{\mathbf{k}}$ and $\sum_{\mathbf{k}} b_{\mathbf{k}}^\dagger b_{\mathbf{k}}$. It means that $\mathcal{L}_c^* M = 0$ and $\mathcal{L}_c^*$ disappears from the formula (8) for the stationary power output. Notice, that in the discussed idealized model heat transport leading to a temperature gradient is neglected what corresponds to the infinite heat conductivity of the bulk.

Hot bath generator and stationary state

The generator $\mathcal{L}_h$ describes thermally induced electron transitions from one box to another across the potential barrier and can be written in the following form

$$\mathcal{L}_h[0] = \sum_{\mathbf{kl}} \mathcal{L}_{\mathbf{kl}}^{(h)} \quad (12)$$

where

$$\begin{aligned} \mathcal{L}_{\mathbf{kl}}^{(h)} \rho = & \gamma_{\mathbf{kl}} (a_{\mathbf{k}} b_{\mathbf{l}}^\dagger \rho b_{\mathbf{l}} a_{\mathbf{k}}^\dagger - \frac{1}{2} \{b_{\mathbf{l}} a_{\mathbf{k}}^\dagger a_{\mathbf{k}} b_{\mathbf{l}}^\dagger, \rho\}) \\ & + e^{-E_g/T_1} \gamma_{\mathbf{kl}} (a_{\mathbf{k}}^\dagger b_{\mathbf{l}} \rho b_{\mathbf{l}}^\dagger a_{\mathbf{k}} - \frac{1}{2} \{b_{\mathbf{l}}^\dagger a_{\mathbf{k}} a_{\mathbf{k}}^\dagger b_{\mathbf{l}}, \rho\}), \end{aligned} \quad (13)$$

The single term (13) describes the following processes:

a) electron transfer from the box A to B accompanied by a positive energy release to the hot bath equal to

$$E_a(\mathbf{k}) - E_b(\mathbf{l}) \simeq E_g, \quad (14)$$

b) the inverse process of electron transfer from the lower energy state in B to the higher energy one in A with the probability suppressed by the Boltzmann factor.

The condition (14) follows from the approximate energy conservation valid for the tunneling process through a barrier of the height E_g assisted by thermal fluctuations of the hot bath. It means also that the relaxation rates $\gamma_{\mathbf{kl}}$ are essentially different from zero only if (14) is satisfied. They are proportional to the spectral density of the hot bath at $\omega_{\mathbf{kl}} = E_a(\mathbf{k}) - E_b(\mathbf{l}) \simeq E_g$.

Although the generator $\mathcal{L}_c^*$ is absent in the formula for power the thermal relaxation of electrons in a given box is the fastest process and hence determines the form of the stationary state $\bar{\rho}$. Within a reasonable approximation one can assume that the stationary state of the electronic systems with the total Hamiltonian $H_0 + \xi M$ is a product of grand canonical ensembles for electrons in both boxes with the same temperature T of the device and different electro-chemical potentials μ_a and μ_b , respectively. The associated density matrix has form

$$\begin{aligned} \bar{\rho}[\xi] = & \frac{1}{Z[\xi]} \exp \left\{ -\frac{1}{T} \sum_{\mathbf{k}} \left[\left(E_a(\mathbf{k}) + \xi E_g \frac{V_J}{V_A} - \mu_a \right) a_{\mathbf{k}}^\dagger a_{\mathbf{k}} \right. \right. \\ & \left. \left. + \left(E_b(\mathbf{k}) - \xi E_g \frac{V_J}{V_B} - \mu_b \right) b_{\mathbf{k}}^\dagger b_{\mathbf{k}} \right] \right\}. \end{aligned} \quad (15)$$

The electro-chemical potentials μ_a, μ_b are determined by the numbers of carriers and hence by densities of electrons in both boxes. The difference of electro-chemical potentials is related to the measured voltage Φ between A and B

$$\mu_a - \mu_b = e\Phi. \quad (16)$$

Power and efficiency

One can insert all elements computed in the previous section into the expression for power (8). Then one uses the properties of the quasi-free (fermionic Gaussian) stationary state (15) which allow to reduce the averages of

even products of annihilation and creation fermionic operators into sums of products of the only non-vanishing two-point correlations

$$\begin{aligned}\langle a_{\mathbf{k}}^\dagger a_{\mathbf{k}'} \rangle_0 &= \delta_{\mathbf{k}\mathbf{k}'} f_c(\mathbf{k}), & \langle a_{\mathbf{k}} a_{\mathbf{k}'}^\dagger \rangle_0 &= \delta_{\mathbf{k}\mathbf{k}'} (1 - f_c(\mathbf{k})), \\ \langle b_{\mathbf{l}}^\dagger b_{\mathbf{l}'} \rangle_0 &= \delta_{\mathbf{l}\mathbf{l}'} f_b(\mathbf{l}), & \langle b_{\mathbf{l}} b_{\mathbf{l}'}^\dagger \rangle_0 &= \delta_{\mathbf{l}\mathbf{l}'} (1 - f_b(\mathbf{l})).\end{aligned}$$

Here $\langle \dots \rangle_0$ denotes the quantum average with respect to the state $\bar{\rho}[0]$ given by (15), and $f_a(\mathbf{k})$ and $f_b(\mathbf{l})$ are the Fermi-Dirac statistical distribution functions

$$f_a(\mathbf{k}) = \frac{1}{e^{\beta(E_a(\mathbf{k}) - \mu_a)} + 1}, \quad f_b(\mathbf{l}) = \frac{1}{e^{\beta(E_b(\mathbf{l}) - \mu_b)} + 1}, \quad (18)$$

with $\beta = 1/T$. Inserting the elements defined above into the general formula (8) one obtains the leading order contribution to power in a following form

$$\begin{aligned}\bar{P} &= \frac{g^2 E_g^2 V_J^2}{T} (V_A + V_B) (\bar{n}_b - \bar{n}_a) \times \\ &\frac{1}{V_A V_B} \sum_{\mathbf{k}\mathbf{l}} \gamma_{\mathbf{k}\mathbf{l}} \left(e^{-E_g/T_1} [1 - f_a(\mathbf{k})] f_b(\mathbf{l}) - [1 - f_b(\mathbf{l})] f_a(\mathbf{k}) \right),\end{aligned} \quad (19)$$

where $\bar{n}_a = \frac{1}{V_A} \langle \sum_{\mathbf{k}} a_{\mathbf{k}}^\dagger a_{\mathbf{k}} \rangle_0$, $\bar{n}_b = \frac{1}{V_B} \langle \sum_{\mathbf{l}} b_{\mathbf{l}}^\dagger b_{\mathbf{l}} \rangle_0$ are electron densities. Using (16) one can rewrite (19) as

$$\begin{aligned}\bar{P} &= \frac{g^2 E_g^2 V_J^2}{T} (V_A + V_B) (\bar{n}_b - \bar{n}_a) \Gamma \times \\ &\left(\exp \left\{ \frac{1}{T} \left(\left[1 - \frac{T}{T_1} \right] E_g - e\Phi \right) \right\} - 1 \right),\end{aligned} \quad (20)$$

where $\Gamma = \frac{1}{V_A V_B} \sum_{\mathbf{k}\mathbf{l}} \gamma_{\mathbf{k}\mathbf{l}} [1 - f_b(\mathbf{l})] f_a(\mathbf{k}) > 0$ is finite in the thermodynamical limit.

The condition for work generation in the discussed model of idealized thermoelectric device reads ($\Delta T = T_1 - T$)

$$e\Phi < e\Phi_0 = E_g \left(1 - \frac{T}{T_1} \right) = \frac{E_g}{T_1} \Delta T \quad (21)$$

The inequality in (21) implies that Φ_0 can be interpreted as an *open-circuit voltage* of the device and $\frac{E_g}{eT_1}$ as the *relative Seebeck coefficient*.

By closing the external circuit one reduces the voltage and hence the output power is strictly positive driving collective charge oscillations (positive feedback). The charge oscillations are subsequently rectified by the diode mechanism of the junction producing a direct current.

The presence of the Carnot factor $1 - T/T_1$ suggests also the interpretation of the eq. (21) in terms of thermodynamical efficiency. Indeed, the transport of a single electron from the box B to A through the junction requires at least E_g of thermal energy extracted from the hot bath. Then, a part of energy E_g is transformed into useful work, equal at most $e\Phi_0$ per single electron flowing in the external circuit.

For real systems the efficiency is much smaller than the Carnot bound because of the finite heat conductivity and

damping of plasma oscillations. Similarly, for a typical $T_1 \sim 500K$, the relative Seebeck coefficient given by (21) is of the order of mV/K what is comparable to the highest values obtained for some semiconductors. For metals, the neglected irreversible transport processes reduce the Seebeck coefficient by two or three orders of magnitude.

CONCLUSIONS

The aim of this paper is to show that the idea of “hidden self-oscillations” proposed in [1] for solar cells can be extended to thermoelectric generators. It is illustrated by the idealized model in which heat conduction is neglected. The “moving piston” is again represented by collective charge oscillations with frequencies in the THz domain. While such oscillations are observed in p-n junctions, for bimetallic ones a plausible mechanism of their generation is proposed in the Appendix. The challenging open question is to apply the similar ideas to systems based on organic molecules including “biological engines”.

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Appendix

In the Appendix the arguments for the existence of slow plasma oscillation modes in bimetallic junctions are presented and the origin of diagonal modulation Hamiltonian is explained for both, semiconductor and bimetallic devices. Here, $\hbar$ is put explicitly in the formulas.

Slow charge oscillations in bimetallic junctions

In order to find collective oscillating modes of electron gas in a bimetallic junction one can use the one-dimensional hydrodynamical model. The basic variables are: the electron density $n(x, t)$, the electrical potential $\psi(x, t)$ and the velocity field $v(x, t)$ satisfying the set of coupled equations

$$m_* \frac{\partial}{\partial t} v + v \frac{\partial}{\partial x} v + \frac{1}{n} \frac{\partial}{\partial x} p - e \frac{\partial}{\partial x} \psi = 0 \quad (22)$$

$$\frac{\partial}{\partial t} n + \frac{\partial}{\partial x} (nv) = 0 \quad (23)$$

$$\frac{\partial^2}{\partial x^2} \psi - \frac{e}{\epsilon_0} (n - n_0) = 0. \quad (24)$$

Here m_* is the effective mass of an electron and $n_0 = n_0(x)$ is the time-independent density of background positive ions (jellium model). The pressure $p(x, t)$ is not an independent variable but is given by the standard formula for the degenerated electron gas

$$p = \frac{(3\pi^2)^{2/3} \hbar^2}{2m_*} n^{5/3} \equiv \alpha n^{5/3}. \quad (25)$$

The stationary solution is given by $v = 0$ and the density $\bar{n}(x)$ which up to a certain smoothing essentially follows the background density $n_0(x)$. Consider a small perturbation of the stationary electron gas distribution in a form of well-localized wave packet, i.e. $n(x, t) = \bar{n}(x) + \delta n(x, t)$. Inserting also $\psi(x, t) = \bar{\psi}(x) + \delta\psi(x, t)$ into eqs. (22)-(24) and assuming that the stationary density is a slowly varying function of x in comparison with the variation of the wave packet δn one obtains a set of linearized equations

$$m_* \frac{\partial}{\partial t} v + \frac{5}{3} \frac{\alpha}{\bar{n}^{1/3}} \frac{\partial}{\partial x} \delta n - e \frac{\partial}{\partial x} \delta\psi = 0, \quad (26)$$

$$\frac{\partial}{\partial t} \delta n + \bar{n} \frac{\partial}{\partial x} v = 0, \quad (27)$$

$$\frac{\partial^2}{\partial x^2} \delta\psi - \frac{e}{\epsilon_0} \delta n = 0. \quad (28)$$

Taking the derivative of eq.(26) with respect to x then inserting relations (27),(28) (omitting the derivatives of $\bar{n}$) one obtains the following one-dimensional Klein-Gordon-like equation

$$\left[\frac{\partial^2}{\partial t^2} - c_F^2 \frac{\partial^2}{\partial x^2} + \omega_p^2 \right] \delta n = 0 \quad (29)$$

for the density perturbation δn . Here, the maximal velocity c_F is given by

$$c_F^2 = \frac{5}{3} \frac{(3\pi^2)^{2/3} \hbar^2}{2m_*^2} \bar{n}^{2/3} = \frac{5}{6} v_F^2. \quad (30)$$

where v_F is the Fermi velocity and ω_p is given by (9).

For an inhomogeneous material like a bimetallic junction c_F and ω_p are assumed to be slowly varying functions of x . Using the analogy to the relativistic Klein-Gordon equation one concludes that the center of the localized perturbation δn moves like a fictitious one-dimensional particle with the “relativistic” Hamiltonian

$$H(x, p) = \sqrt{c_F^2(x) p^2 + \hbar^2 \omega_p^2(x)}. \quad (31)$$

The approximate Hamiltonian equations in the “non-relativistic regime” (small p) read

$$\dot{x} = \frac{p}{M}, \quad M = \frac{\hbar \omega_p}{c_F^2} \quad (32)$$

$$\dot{p} = -\frac{\partial}{\partial x} U(x), \quad U(x) = \hbar \omega_p(x). \quad (33)$$

To advocate the existence of slow modes in bimetallic junctions one can propose the qualitative but plausible shape of the effective potential $U(x)$ which interpolates between two bulk values characteristic for both metals (see Fig. 2). The well in the middle can be explained by the presence of a large number of defects in the transition region between two different lattices. Those defects trap a certain number of electrons reducing the density of free electrons and hence also the local value of $\omega_p(x) \sim \sqrt{\bar{n}(x)}$. As the jump of the effective potential $\Delta U = \hbar(\omega_p^{(B)} - \omega_p^{(A)})$ is of the order of few eV one can estimate the depth of the well as $\Delta E = 0.1 - 1 \text{ eV}$ (still higher than the typical value of $T_1 \simeq 0.05 \text{ eV}$) and a reasonable value for its width as $L = 100 \text{ nm}$ (comparable to a typical roughness of well polished metallic surfaces). Using the harmonic well approximation $U(x) \simeq \frac{1}{2} M \Omega^2 x^2$ one can estimate the oscillation frequency of the plasmonic wave packet confined in the well by

$$\Omega = \sqrt{\frac{2\Delta E}{ML^2}}. \quad (34)$$

Taking typical values $\omega_p \simeq 10^{15} \text{ s}^{-1}$ and $v_F \simeq 10^6 \frac{\text{m}}{\text{s}}$ one obtains $M \simeq 10^{-30} \text{ kg}$ and hence, finally $\Omega \simeq 1 \text{ THz}$ - the value comparable to that for plasma oscillations in semiconductor p-n junctions.

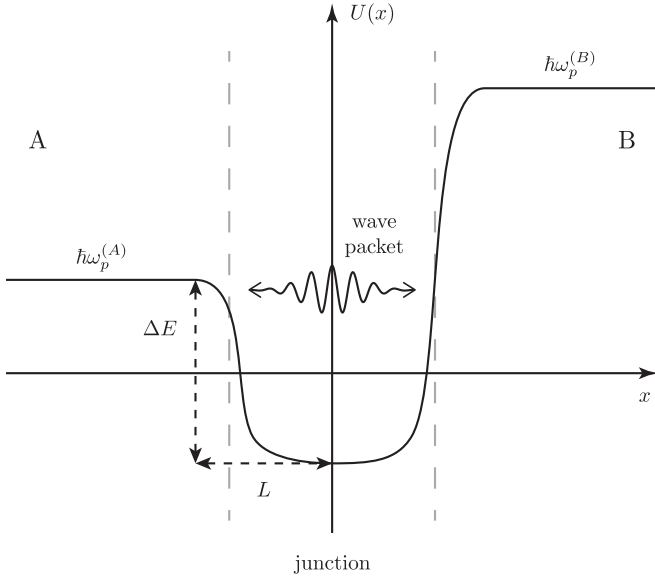


FIG. 2. **Bimetallic junction.** The shape of the effective potential for the plasmonic wave packet. It is instructive to compare the proposed shape of $U(x)$, proportional to $\sqrt{\bar{n}(x)}$, with the very similar shape of electron number density obtained numerically in [12] for the case of Al-Mg contact. In [12] (FIG.1) the ideal plane surfaces are separated by a small distance of $0.3nm$. This gap produces physical effects similar to the real metal-metal interface.

Effective modulation Hamiltonians

The aim of this section is to justify the choice of the diagonal modulation as a generic consequence of the weak coupling between the system and the driving oscillations.

Consider first the case of slow and weak perturbation described by the Hamiltonian $H_0 + \lambda V(t)$ which is applicable to p-n junction. For a fixed t one can apply the lowest order of the standard perturbation theory for approximate eigenvectors and eigenenergies

$$\phi_j \simeq \phi_j^{(0)}, \quad (35)$$

$$E_j \simeq E_j^{(0)} + \lambda \langle \phi_j^{(0)} | V | \phi_j^{(0)} \rangle. \quad (36)$$

Within this approximation one can use the effective time-dependent Hamiltonian with diagonal perturbation

$$H(t) = H_0 + \lambda \sum_j \langle \phi_j^{(0)} | V(t) | \phi_j^{(0)} \rangle | \phi_j^{(0)} \rangle \langle \phi_j^{(0)} |. \quad (37)$$

For the case of bimetallic junction one should take into account the fact that the source of perturbation is a “wave packet” with fast “internal” charge oscillations at the frequency ω_p and slow oscillatory motion of its envelope. Hence, the resulting time-dependent Hamiltonian possesses the following structure

$$H(t) = H_0 + \lambda [f(t) \cos \omega_p t] V, \quad (38)$$

where $f(t)$ describes the slowly varying envelope. In this case the terms linear in λ are practically averaged out. Using the second order of the standard perturbation theory

$$\phi_j \simeq \phi_j^{(0)} + \lambda \sum_{k \neq j} \frac{\langle \phi_k^{(0)} | V | \phi_j^{(0)} \rangle}{E_j^{(0)} - E_k^{(0)}} \phi_k^{(0)}. \quad (39)$$

$$E_j \simeq E_j^{(0)} + \lambda \langle \phi_j^{(0)} | V | \phi_j^{(0)} \rangle + \lambda^2 \sum_{k \neq j} \frac{|\langle \phi_k^{(0)} | V | \phi_j^{(0)} \rangle|^2}{E_j^{(0)} - E_k^{(0)}}, \quad (40)$$

and averaging over fast oscillations one obtains the following effective Hamiltonian

$$H(t) = H_0 + \frac{1}{2} \lambda^2 f^2(t) \sum_j \sum_{k \neq j} \frac{|\langle \phi_k^{(0)} | V | \phi_j^{(0)} \rangle|^2}{E_j^{(0)} - E_k^{(0)}} | \phi_j^{(0)} \rangle \langle \phi_j^{(0)} | \quad (41)$$

with, again, diagonal modulation term.

Notice, that for the bimetallic junction the coupling of electrons to charge oscillations is the second order effect and hence, much weaker than for the semiconductor devices. However, this is compensated by much higher electron densities in metals.